

# DL-3147-161(-261)

## Index Guided AlGaInP Laser Diode

#### Overview

DL-3147-161(-261) is index guided 650 nm (Typ.) AlGaInP laser diode with low threshold current and high operating temperature. The low threshold current and high operating temperature are achieved by a strained multiple quantum well active layer. DL-3147-161(-261) is suitable for applications such as optical disc systems (DVD-ROM) and other optical information systems.

#### **Features**

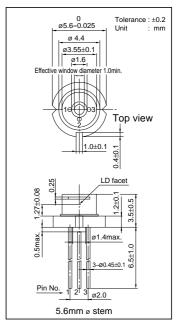
•Short wavelength : 650 nm (Typ.) •Low threshold current : Ith = 45 mA (Typ.) •High operating temperature : 5 mW at 70°C

•TE mode°C

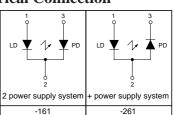
## Absolute Maximum Ratings at Tc=25°C

Parameter		Symbol	Ratings	Unit	
Light Output		Po	7	mW	
Reverse Voltage	Laser PIN	VR	2 30	V	
Operating Temperature		Topr	-10 to +70	°C	
Storage Temperature		Tstg	-40 to +85	°C	

#### **Package Dimensions**



#### **Electrical Connection**



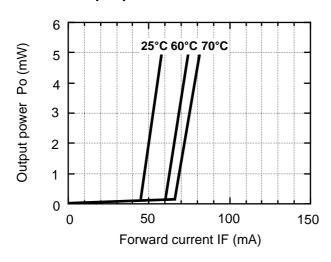
### Electrical and Optical Characteristics at Tc=25°C

Para	meter	Symbol	Condition	Min.	Тур.	Max.	Unit
Threshol	d Current	Ith	CW	-	45	65	mA
Operatin	g Current	Iop	Po=5mW	-	60	80	mA
Operatin	g Voltage	Vop	Po=5mW	-	2.2	2.5	V
Lasing W	avelength	λр	Po=5mW	-	650	660	nm
Beam **)	Perpendicular	$\theta \perp$	Po=5mW	25	30	40	deg.
Divergence	Parallel	$\theta$ //	Po=5mW	6	7.5	10	deg.
Off Axis	Perpendicular	$\Delta  heta \perp$	-	-	-	±3	deg.
Angle	Parallel	$\Delta  heta$ //	-	-	-	±2	deg.
Differentia	l Efficiency	dPo/dIop	-	0.15	0.35	-	mW/mA
Monitoring Output Current		Im	Po=5mW	0.05	0.15	0.5	mA
Astigmatism		As	Po=5mW	-	8	_	μm

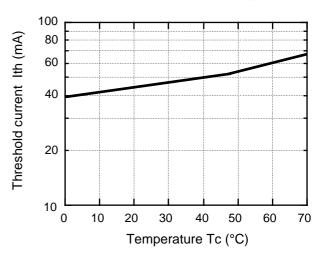
\*) Full angle at half maximum note: The above product specifications are subject to change without notice.

#### **Characteristics**

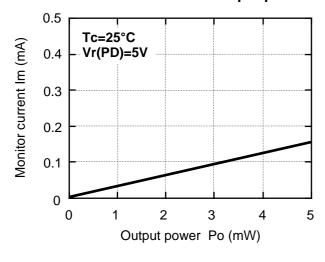
#### Output power vs. Forward current



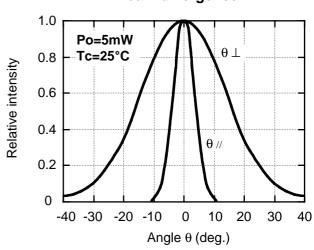
### Threshold current vs. Temperature



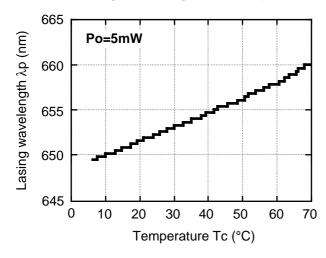
Monitor current vs. Output power



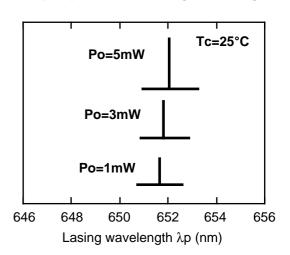
Beam divergence



#### Lasing wavelength vs. Temperature



Output power vs. Lasing wavelength



Relative intensity



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## Precautionary instructions in handling gallium arsenic products

Special precautions must be taken in handling this product because it contains, gallium arsenic, which is designated as a toxic substance by law. Be sure to adhere strictly to all applicable laws and regulations enacted for this substance, particularly when it comes to disposal.

Manufactured by; Tottori SANYO Electric Co., Ltd.

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